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ISSCC 2013 RF Highlights

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03/01/2013

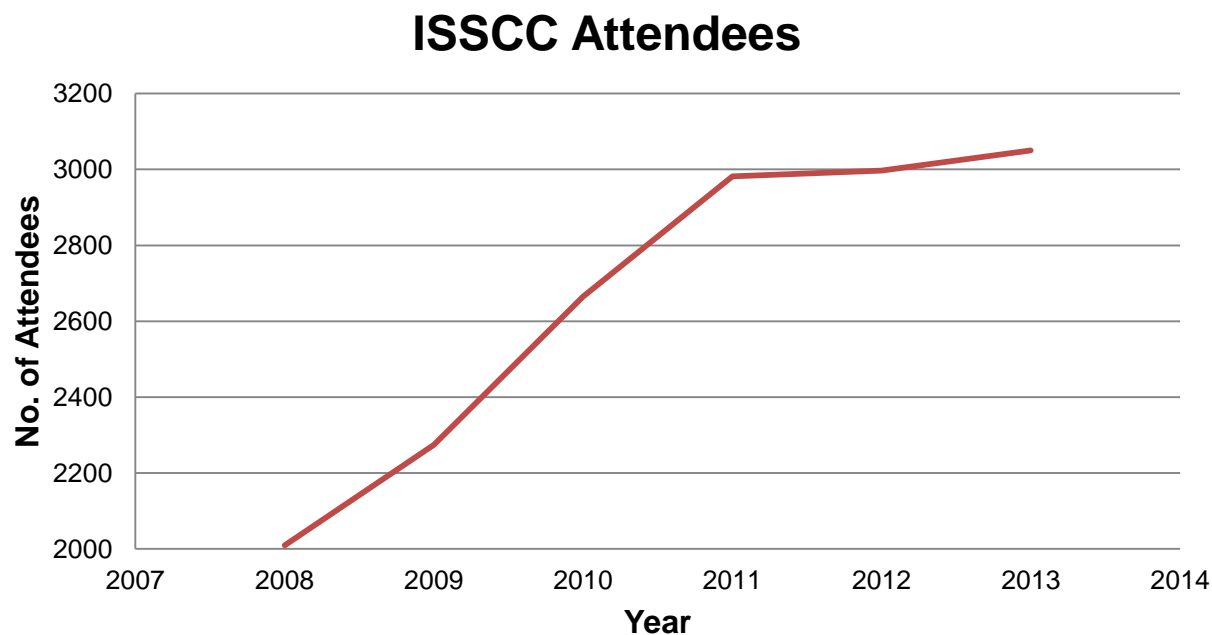
Outline

- **60th anniversary of ISSCC**
- **Paper Statistics**
- **RF Techniques**
- **Frequency Generation Techniques**

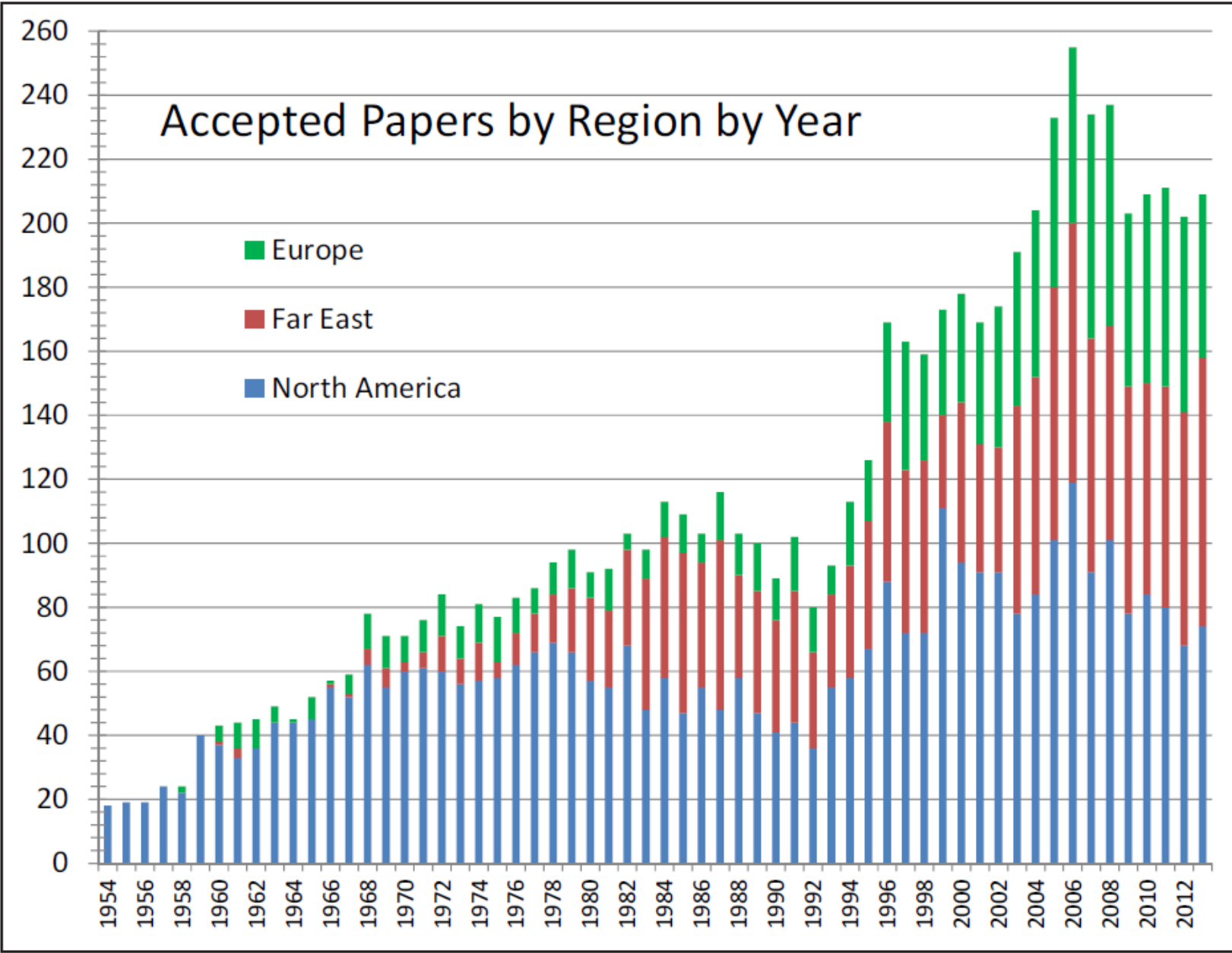
Special Celebrations

➤ **60th anniversary of ISSCC (1954-2013)**

➤ **Lots of nostalgic anecdotes and statistics**



Special Celebrations (cont.)



Overall papers statistics

➤ 209 papers were presented

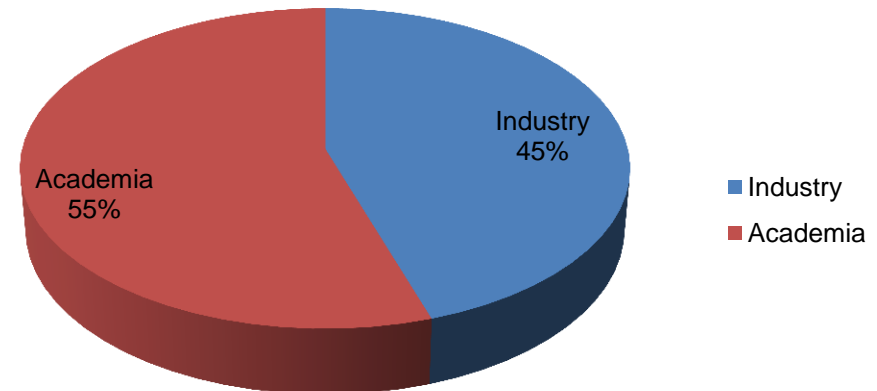
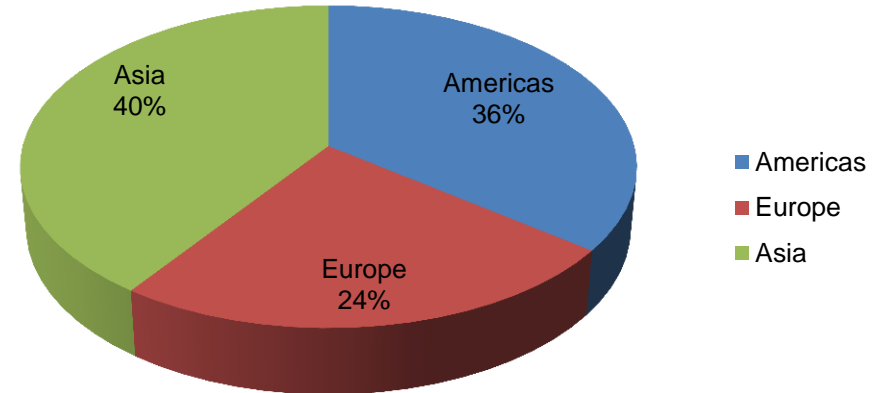
- About the same as last year (206)
- Organized in 27 sessions

➤ Out of the 94 papers from industry, 16 were from the institutes

➤ The papers were uniformly distributed

- Geographically
- Academy vs. industry

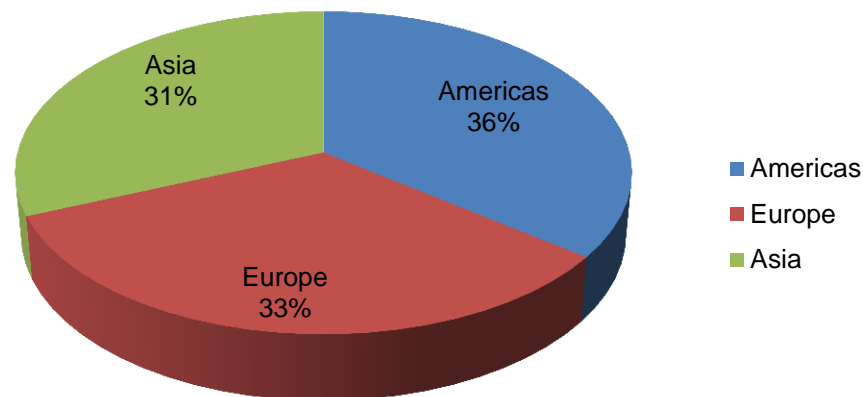
➤ Number of papers from Asia is increasing appreciably



RF paper statistics

➤ RF session titles:

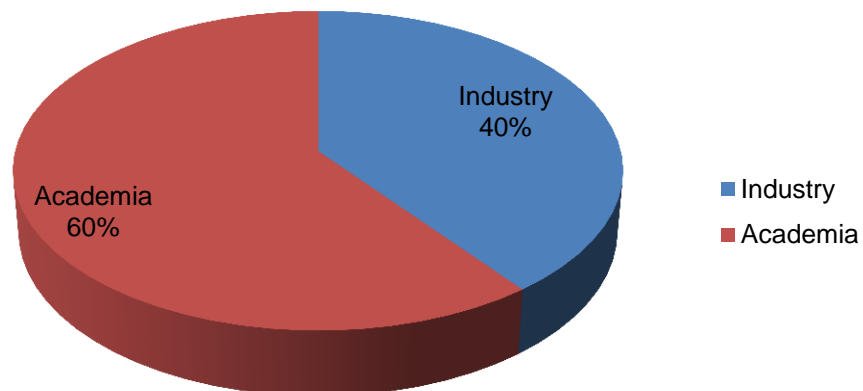
- RF Techniques
- mm-wave Techniques
- High Performance Wireless
- Wireless Transceivers for Smart Devices
- Frequency Generation
- Energy Efficient Wireless



➤ US and Academia had a larger share

➤ RF Forums

- Advanced RF Transceiver Design Techniques
- Mixed Signal/RF Design and Modeling in Next Generation CMOS RF Short courses



5.1: SAW-less Front-End for TDD/FDD

➤ Out-of-band interferes

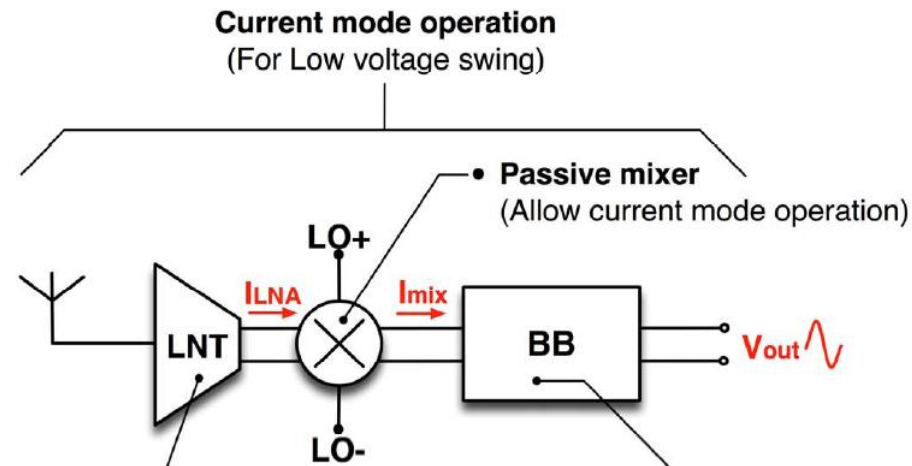
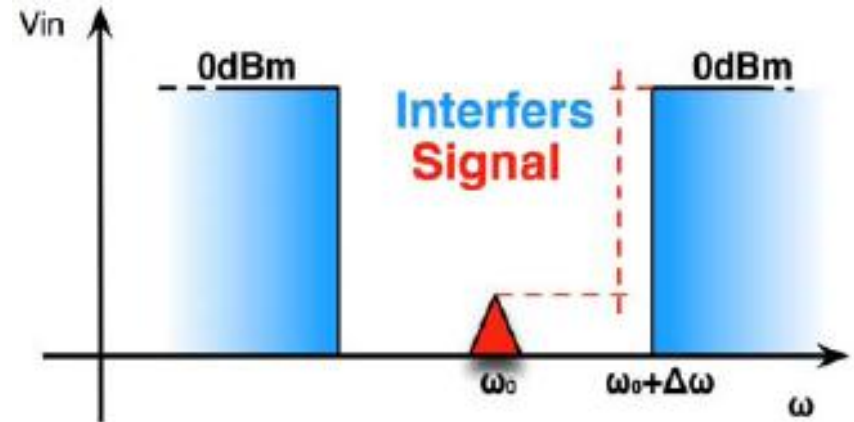
- Dynamic Range (De-sensitization)
- LO Harmonics
- Reciprocal Mixing

➤ External SAW filter

- Resolves the above issues
- Single-ended to differential
- Cost

➤ Current-mode signal processing

- LNA acts as a V/I converter
- I/V conversion after BB filtering
 - Blockers removed in current domain



5.1: SAW-less Front-End for TDD/FDD (cont.)

➤ The bottle neck is the LNA V/I

- Linearity is set by this G_m

➤ CG for Wide-band Z_{in}

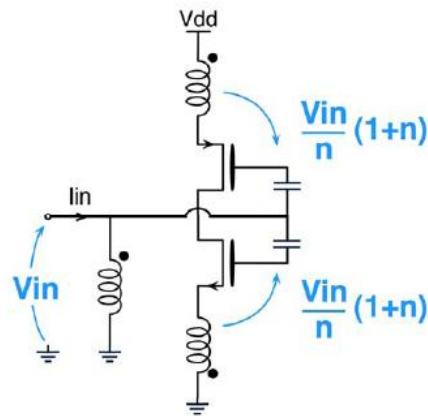
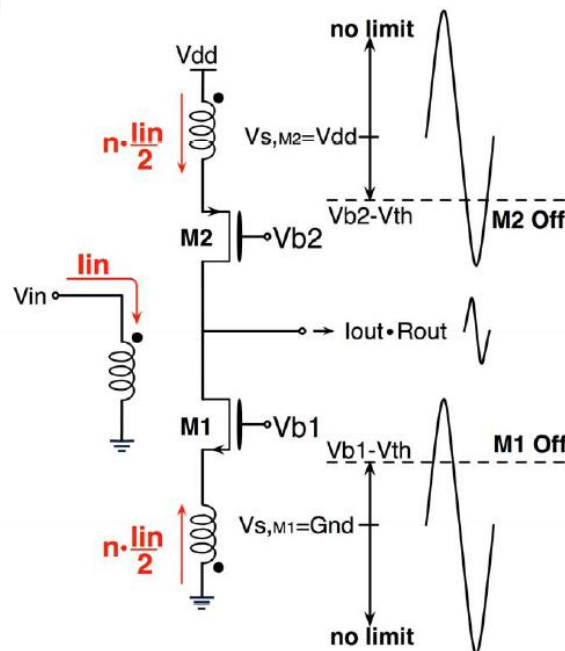
- No current gain
- $NF = 1 + \Gamma = 3$ (too high)

➤ On-chip transformers

- Allows SE/Diff conversion
- Provides maximum headroom
- Provide current gain and negative V_{in}

➤ Use gate boosting

- Apply the signal to the gate
- Improve NF



$$Z_{in} = \frac{n^2}{2g_m(1+n)}$$

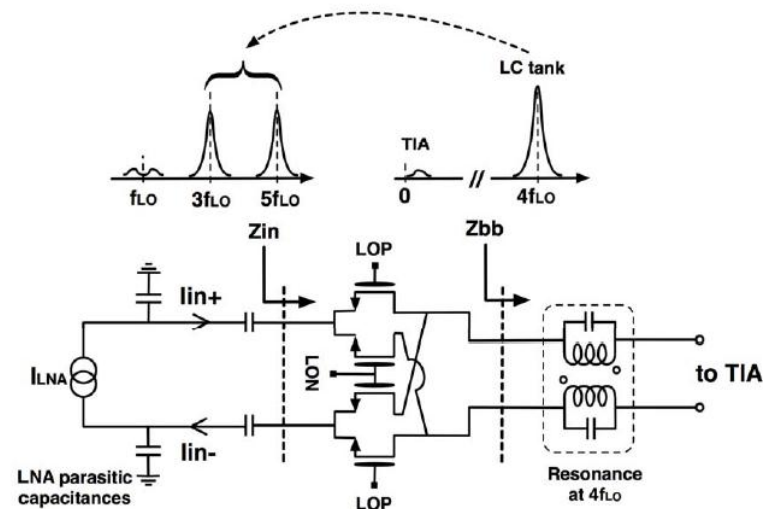
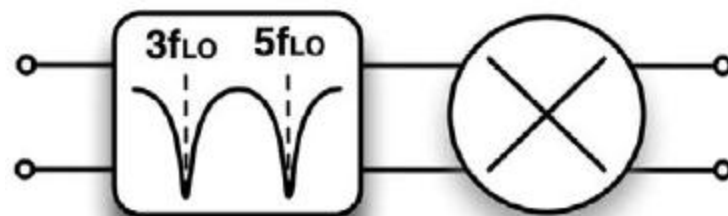
$$NF = 1 + \frac{\gamma}{1+n}$$



5.1: SAW-less Front-End for TDD/FDD (cont.)

- LO Harmonics are still an issue
- One approach is harmonic-Rejection Mixer
 - Needs higher VCO frequencies
- 25% duty-cycle mixer is used
 - The down converted mixer current is passed through an LC network
 - Resonance at $4*f_{LO}$
 - Mixing at f_{LO} converts the notches to
 - $3*f_{LO}$ and $5*f_{LO}$
- Some debate though
 - LO harmonic rejection seems to be limited
 - Mixing also with $3*f_{LO}$ and $5*f_{LO}$
- 40nm CMOS process

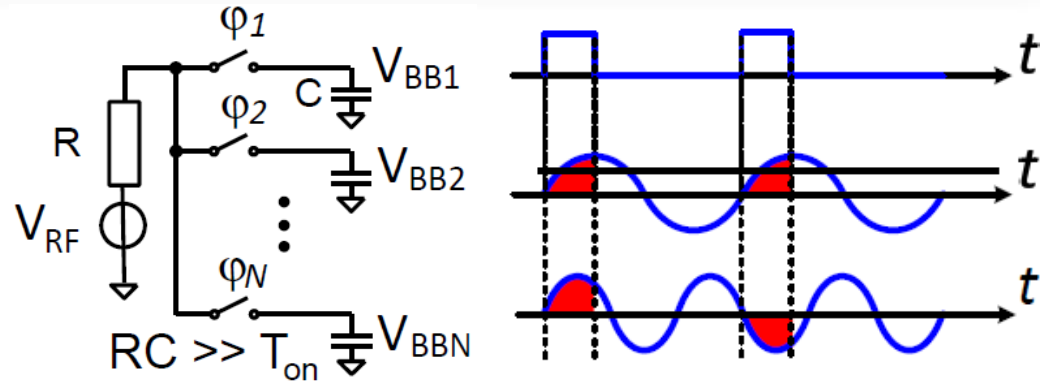
Equivalent mixer model



5.2: Spatial and Frequency Filtering

➤ N-path filtering

- High-Q tunable RF filters
- High RF Imp. for $f_{RF} = f_{LO}$
- Low RF Imp. for $f_{RF} \neq f_{LO}$



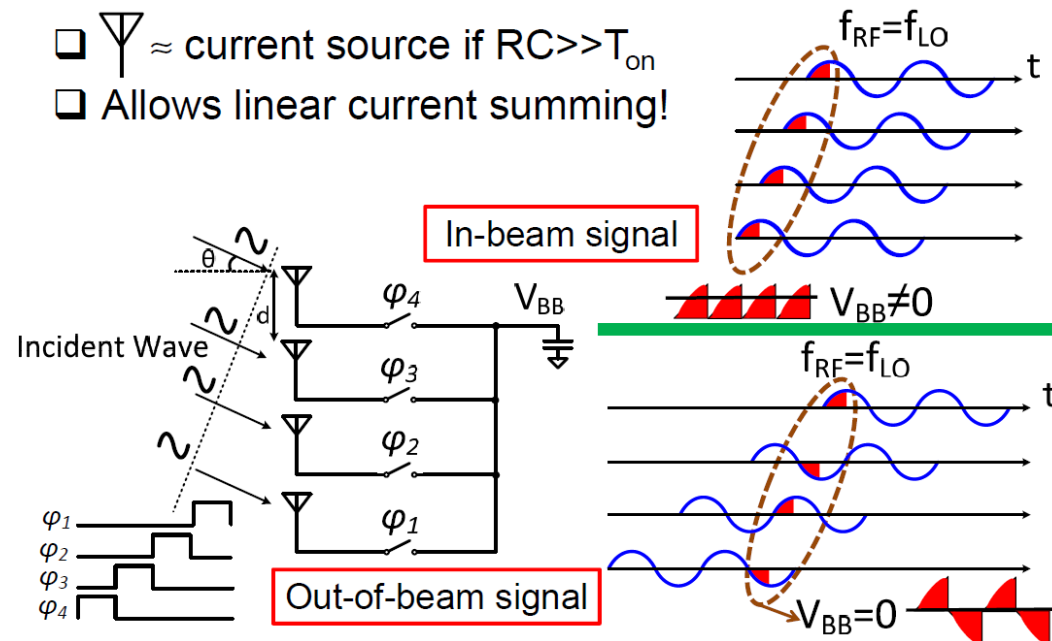
➤ Better Linearity

- No active component at RF

- $\nabla \approx$ current source if $RC \gg T_{on}$
- Allows linear current summing!

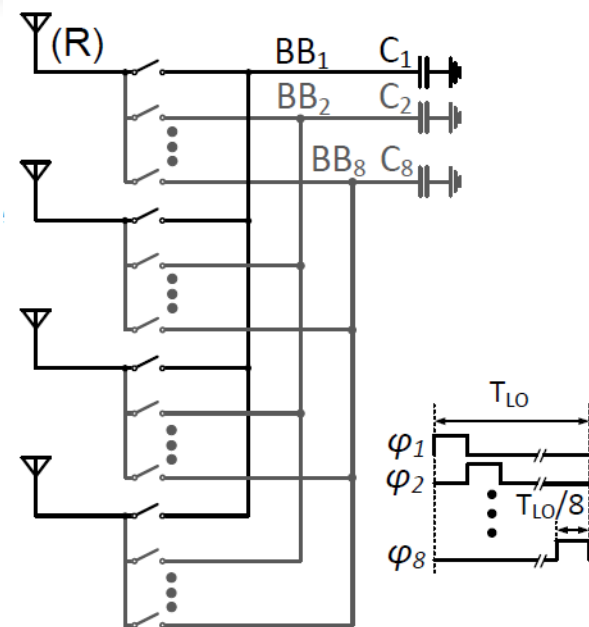
➤ Extend to phase-array

- $RC > T_{on}$
- Antenna is a current source
- Signals add up in C_{BB}
 - Constructively for in-beam
 - Destructively for out-of-beam
- SNR improvement
 - Signals are correlated, noise is not



5.2: Spatial and Frequency Filtering (cont.)

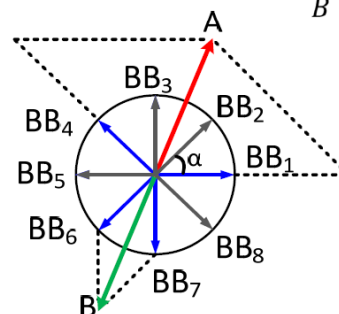
- **Combine the two ideas**
 - Four antennas
 - 8-path filtering for each
 - 8-phase mixer
 - Steer the beam at $N \cdot 90/8$
- **Harmonic rejection is still an issue**
 - $N \cdot f_{LO}$ goes through
- **In this case, $3 \cdot f_{LO}$ is targeted not f_{LO}**
- **Use base-band weights**
 - $3 \cdot f_{LO}$ phase is three times that of f_{LO}
 - Apply BB weights
 - Constructively add for $3 \cdot f_{LO}$
 - Destructively add for f_{LO}
- **65nm CMOS**



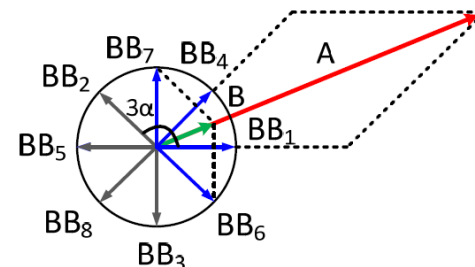
Basis: 3rd harmonic = 3 x phase @ fundamental

$$\vec{A} = (1 + \sqrt{2})(\vec{BB}_1 + \vec{BB}_4)$$

$$\vec{B} = (\vec{BB}_6 + \vec{BB}_7)$$



1st Harmonic $\vec{A} + \vec{B} = 0$



3rd Harmonic $\vec{A} + \vec{B} \neq 0$

3rd harmonic received & 1st harmonic rejected

5.3: Phase noise cancellation

➤ If Phase noise can be cancelled, then

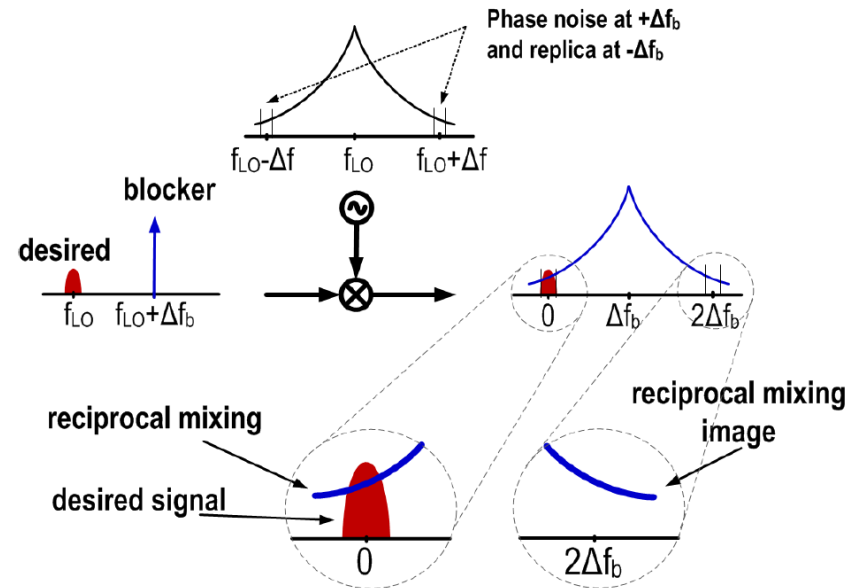
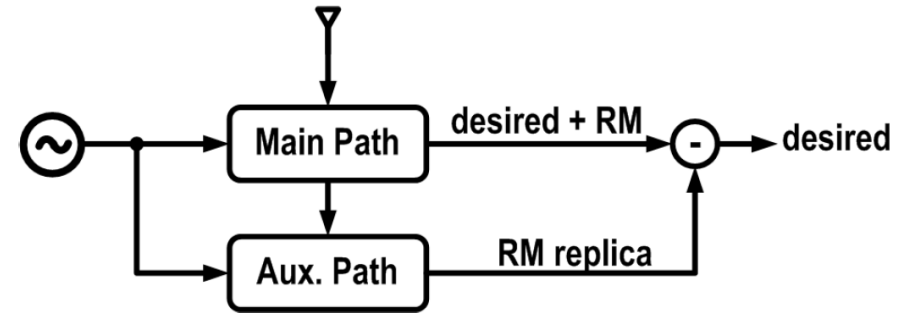
- Use R.O. instead of LC Osc.
- But how?

➤ Use a replica path

- But replica of what?

➤ Phase noise is symmetric

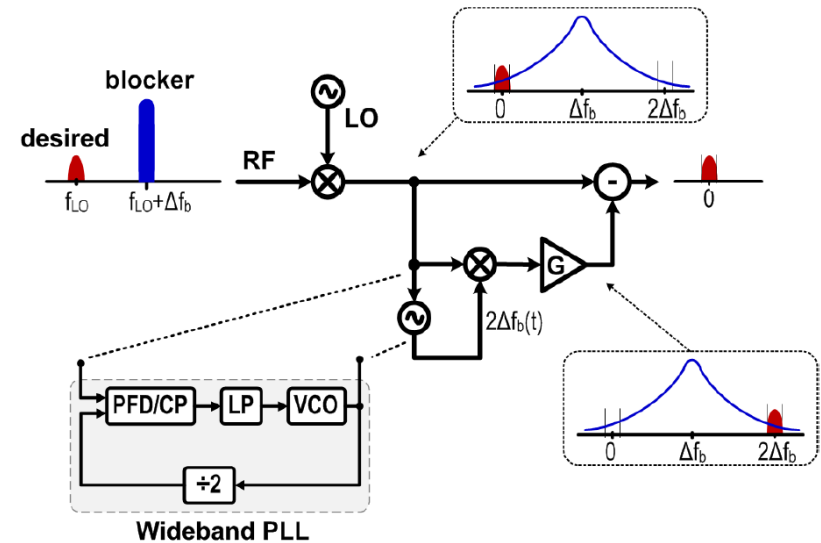
- A copy of the phase noise exists
- Extract it and subtract it
- Let's see how it is done



5.3: Phase noise cancellation (cont.)

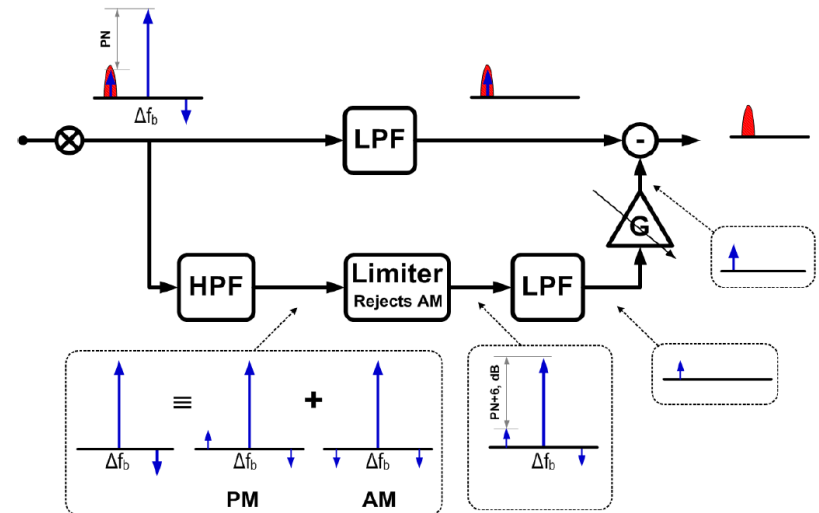
➤ Overall Concept

- Main path: Direct down conversion
- Aux path: Down convert the image
- Not very practical
 - Needs a second synthesizer
 - Phase noise of 2nd synthesizer



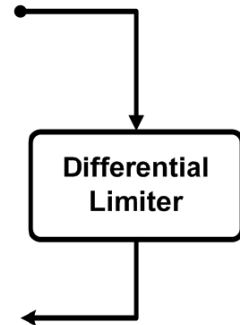
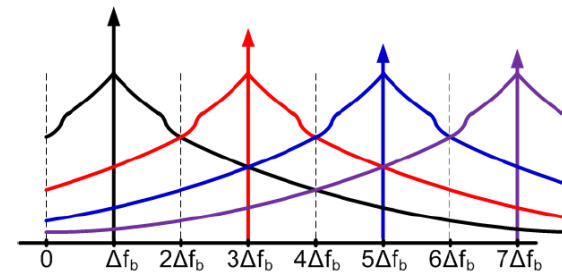
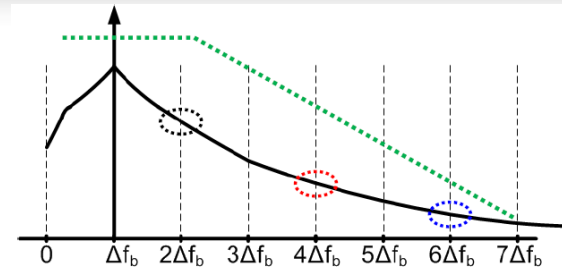
➤ Use a limiter based approach

- Symmetric spurs \rightarrow AM
- Anti-symmetric spurs \rightarrow PM
- Limiter only allows PM through
- Adjust gain and delay for proper cancellation

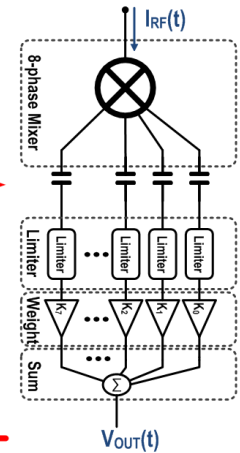
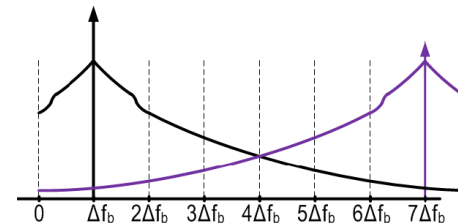
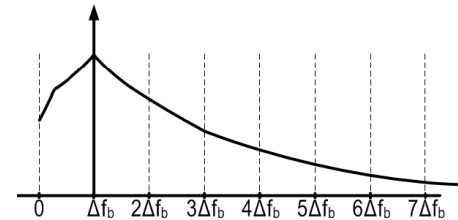


5.3: Phase noise cancellation (cont.)

- **Limiter acts as a PN mixer**
 - Sampling at zero-crossings ($2\Delta f_b$)
 - Folding and images will emerge
 - This will impact the PM subtraction



- **Use an N-phase approach**
 - With proper weighting the first N-2 images will be cancelled.
 - The first image is then at N-1 (smaller impact)



5.3: Phase noise cancellation (cont.)

➤ Final Design

- All circuits are differential
- Inverters are used for all TIA's
- Inv. Also act as limiters
- What about gain calibration?

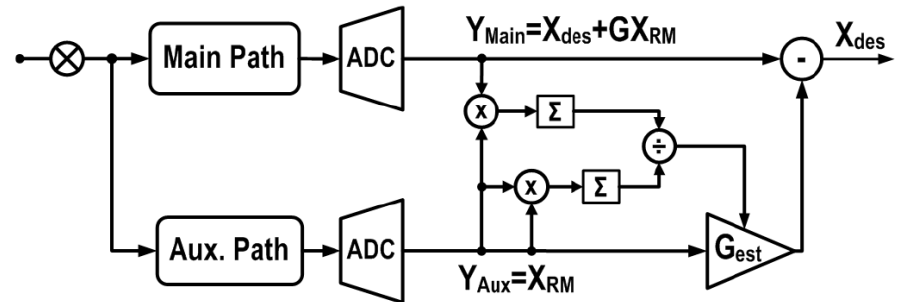
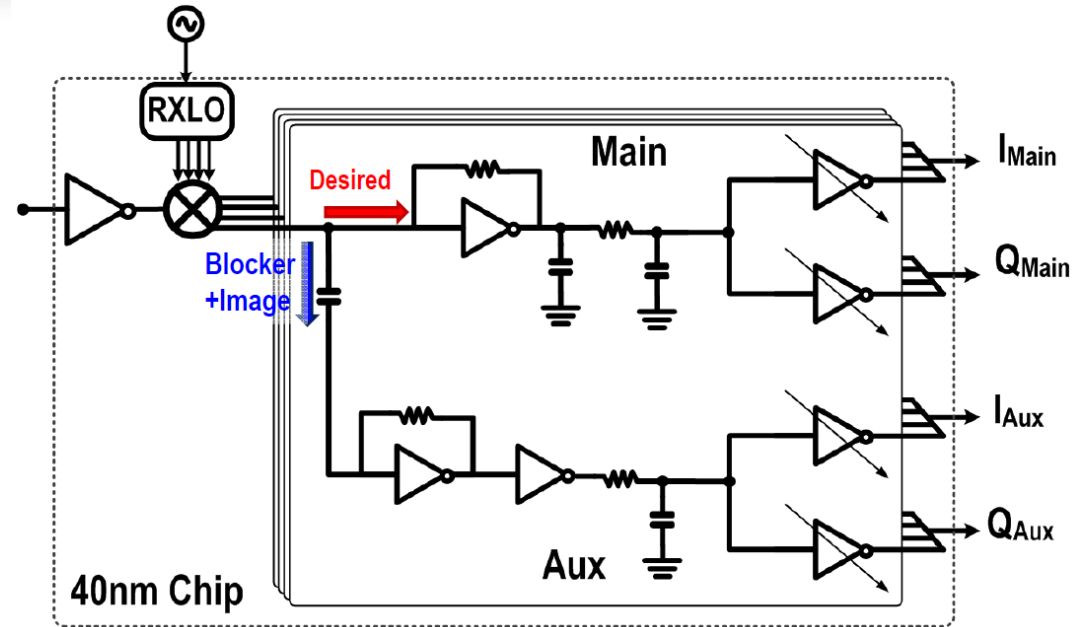
➤ Digitize both paths

- Off chip LMS algorithm
- X_{RM} exists in both paths
 - Causes correlation
 - Provides proper G
- Rest is uncorrelated
 - Long enough averaging will remove this extra signal

➤ Blocker detector

- If no blocker, turn off Aux path

➤ 40nm CMOS



$$G_{est} = \frac{\sum_n Y_{Main}[n] * Y_{Aux}[n]}{\sum_n Y_{Aux}[n] * Y_{Aux}[n]} = G + \frac{\sum_n X_{des}[n] * X_{RM}[n]}{\sum_n X_{RM}^2[n]}$$

Because X_{RM} and X_{des} are statistically independent

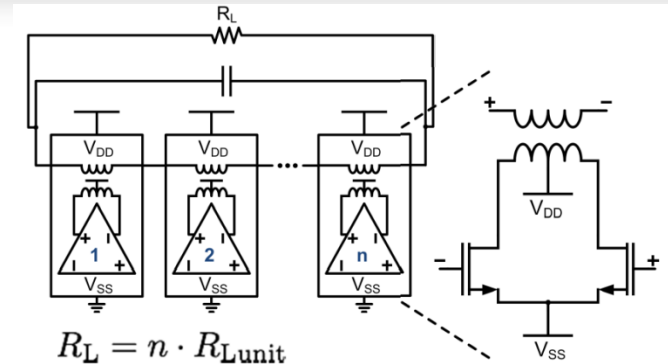
5.4: Stacked Array PA

➤ Array PA's

- Serial
 - Too high an output impedance
- Parallel
 - Too low an output impedance
- Both inefficient due to large impedance ratios
 - High Q → High IL (for a given Q_{comp})

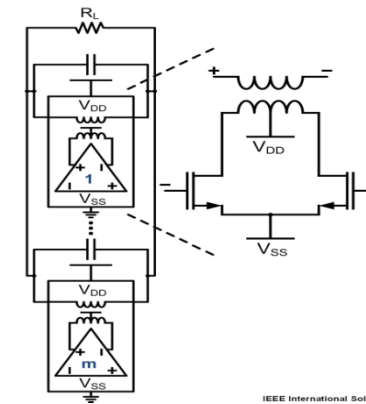
➤ Use arrays of S/P instead

- Can provide better matching
 - Lower impedance ratio
 - Better efficiency



$$R_L = n \cdot R_{Lunit}$$

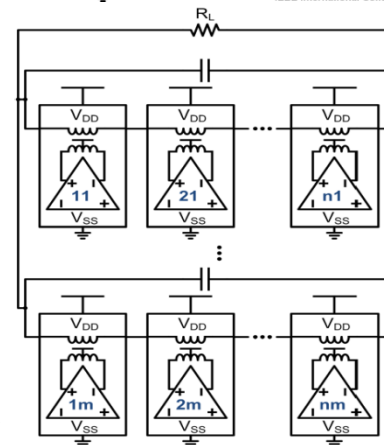
$$P_{out} = n \cdot P_{unit}$$



$$R_L = R_{Lunit}/m$$

$$P_{out} = m \cdot P_{unit}$$

B. Martineau *et al.*, ISSCC, 2010



$$R_L = R_{Lunit} \cdot n/m$$

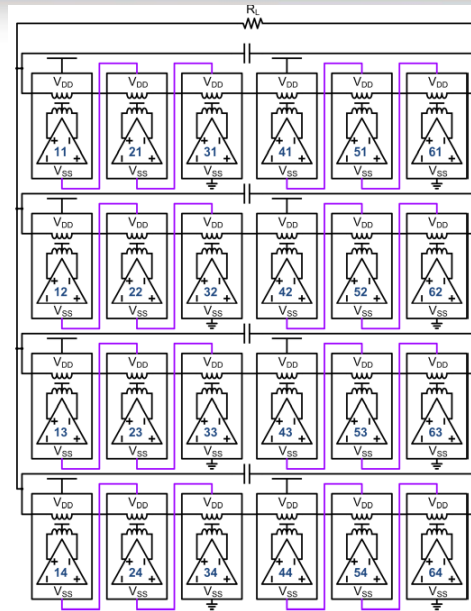
$$P_{out} = n \cdot m \cdot P_{unit}$$

- Scalable
- Flexible

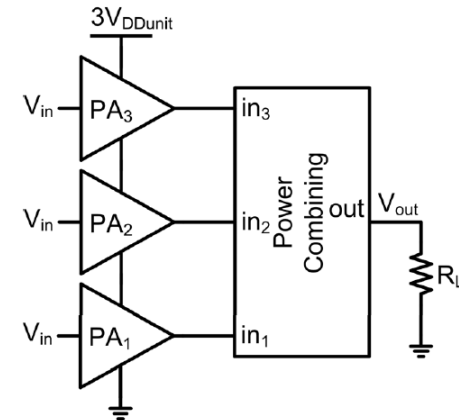
J.-W. Lai *et al.*, ISSCC, 2010

5.4: Stacked Array PA (cont.)

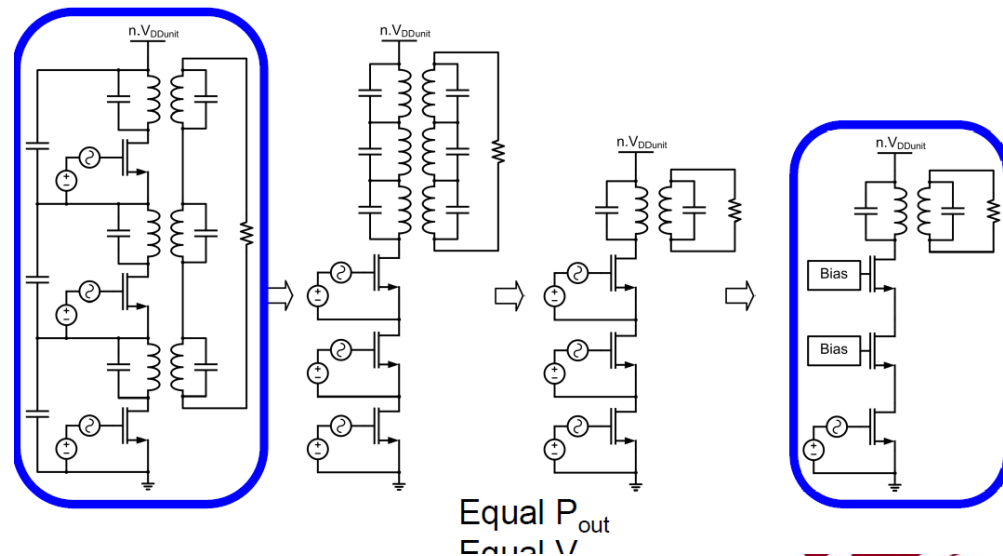
- **Large swing is an issue**
 - Hot Carrier Injection
 - Oxide dielectric breakdown
- **Use stacking**
 - Distribute the swing and supply across several series devices
 - Too many transformers
 - Hard to route
- **Merge transformers into one**
 - Simplify the design
 - Enhance the power routings
 - Use HV for the top most device
 - Needs to handle large V_{db}
 - Parasitic S/D caps affect efficiency



- ❑ $n = 6, m = 4$
- ❑ Stacking 3 stages*



* A. Ezzeddine et al., MTT-S, June 1985



5.4: Stacked Array PA (cont.)

➤ C_p along with R_{on} (when in triode) causes loss

- During charge and discharge

➤ Often inductors are used to tune

- Cost
- Narrow band

➤ Use negative capacitors

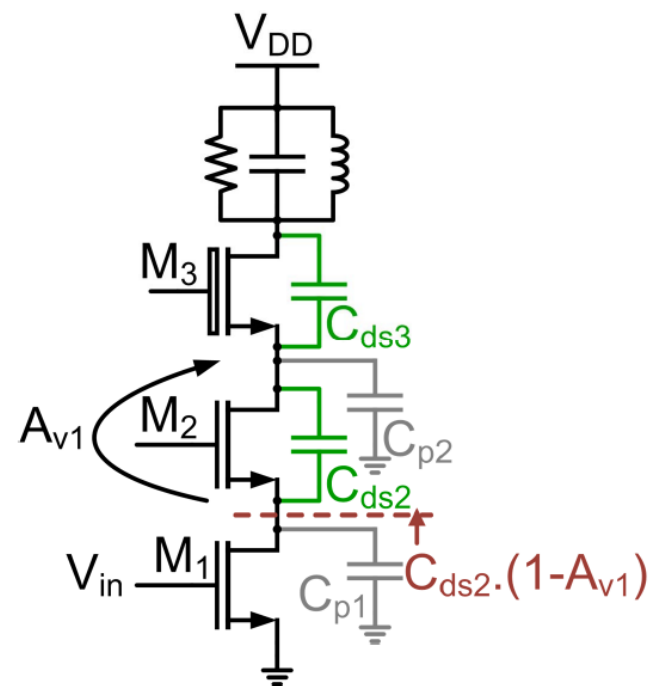
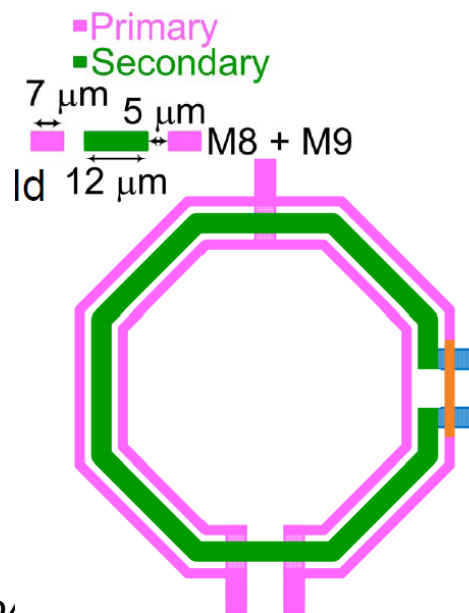
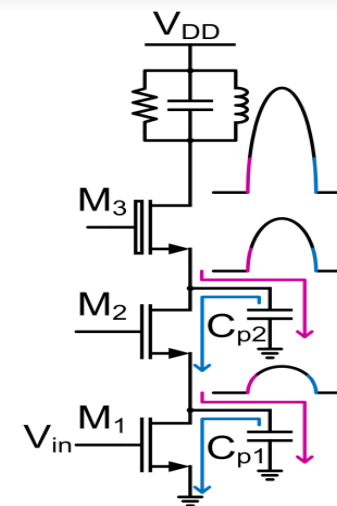
- Wide-band
- But how?
- Use Miller effect

➤ Transformers design

- Low lateral and secondary caps

➤ 65nm CMOS

- $P_{out} = 28\text{dBm}$, $PAE = 20.6\%$



5.5: Supply switching PA

➤ Efficiency degrades when PA B.O.

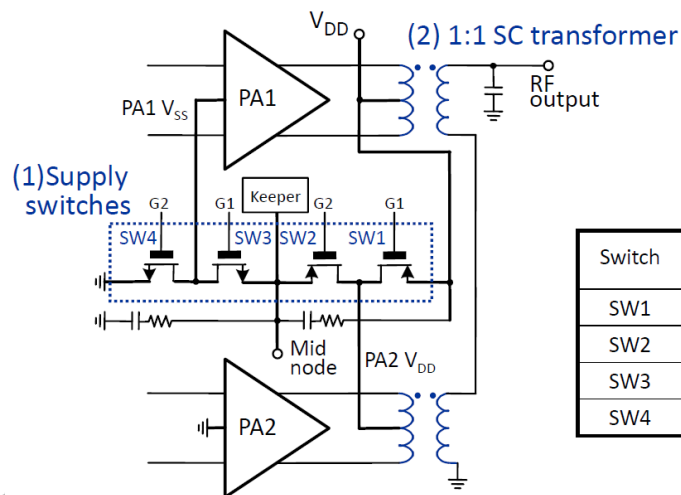
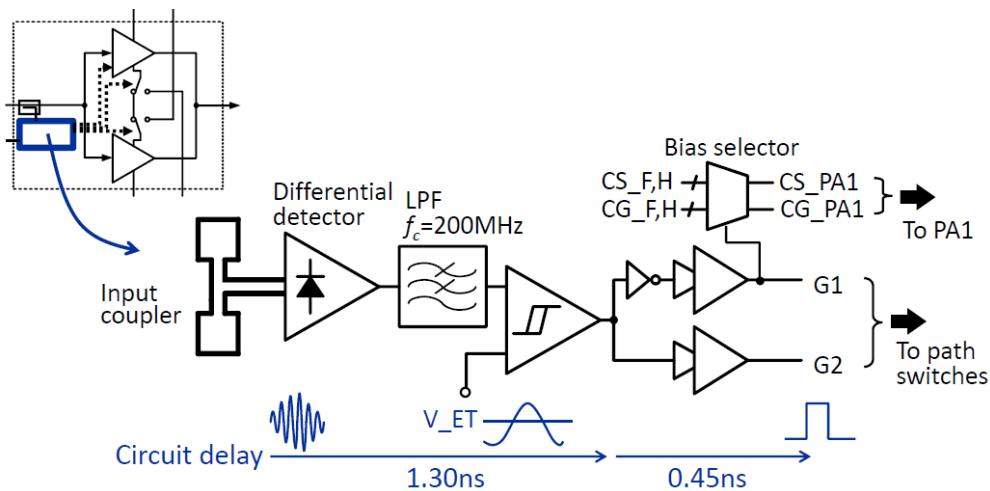
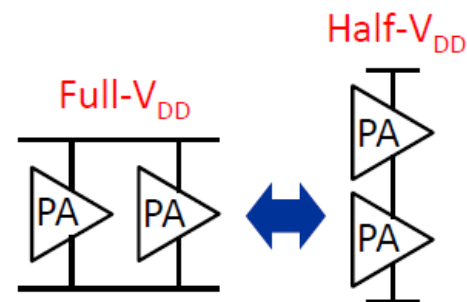
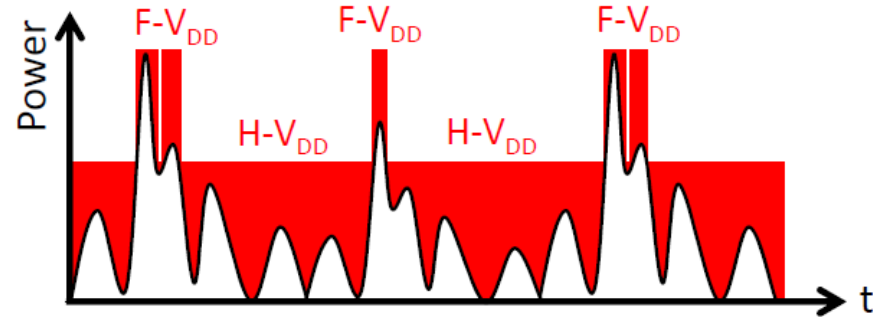
➤ What is supply drops when signal drops?

- Needs DC/DC converters
- Use stacked PA for $V_{DD}/2$ case
 - Mid point needs to be around $V_{DD}/2$
 - Use a keeper

➤ <2ns threshold detector (EVM Impact)

- Some switching noise issues

• Dynamic Operation (Envelope Tracking)



Switch	Channel width (mm)
SW1	7.5
SW2	25.5
SW3	7.5
SW4	5.0

5.6: TX leakage suppression

➤ RFID system

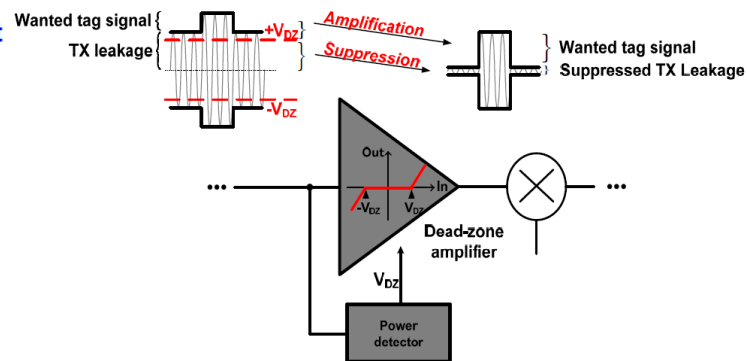
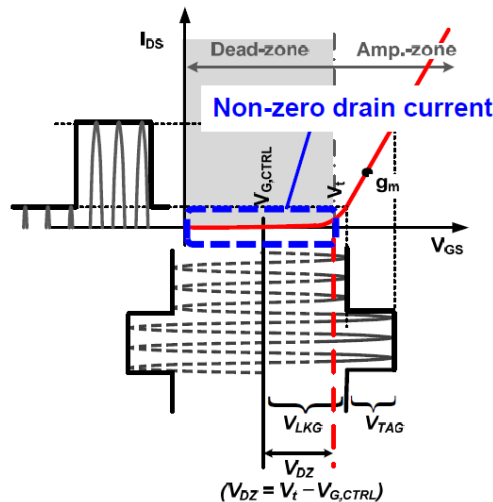
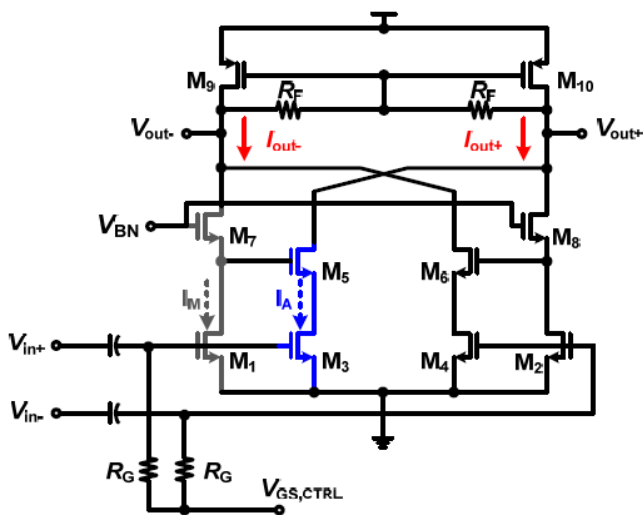
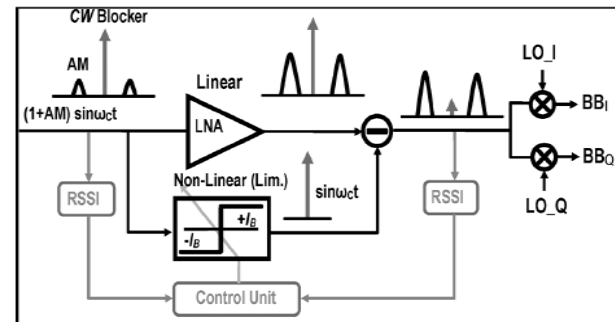
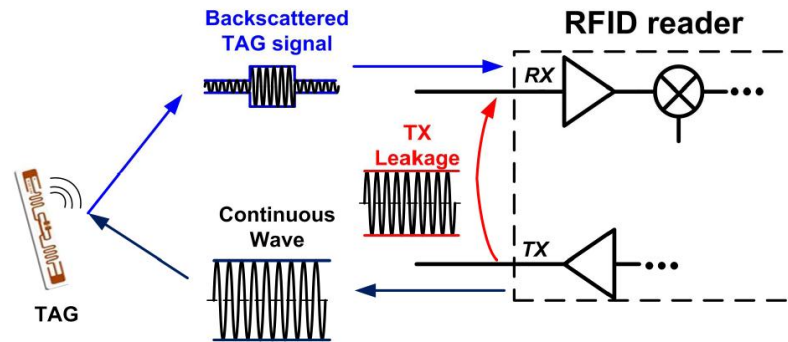
- Back scatter and AM modulate an incoming CW
- RX signal contaminated by the TX CW

➤ Current techniques

- Active blocker injection
- VCO cancellation

➤ Proposed solution

- Non-linear amplification with a dead zone



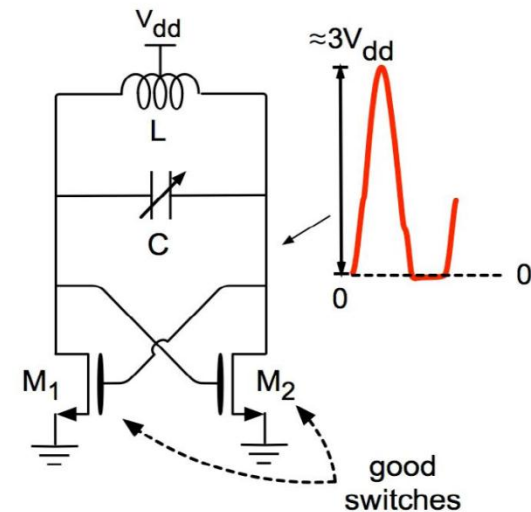
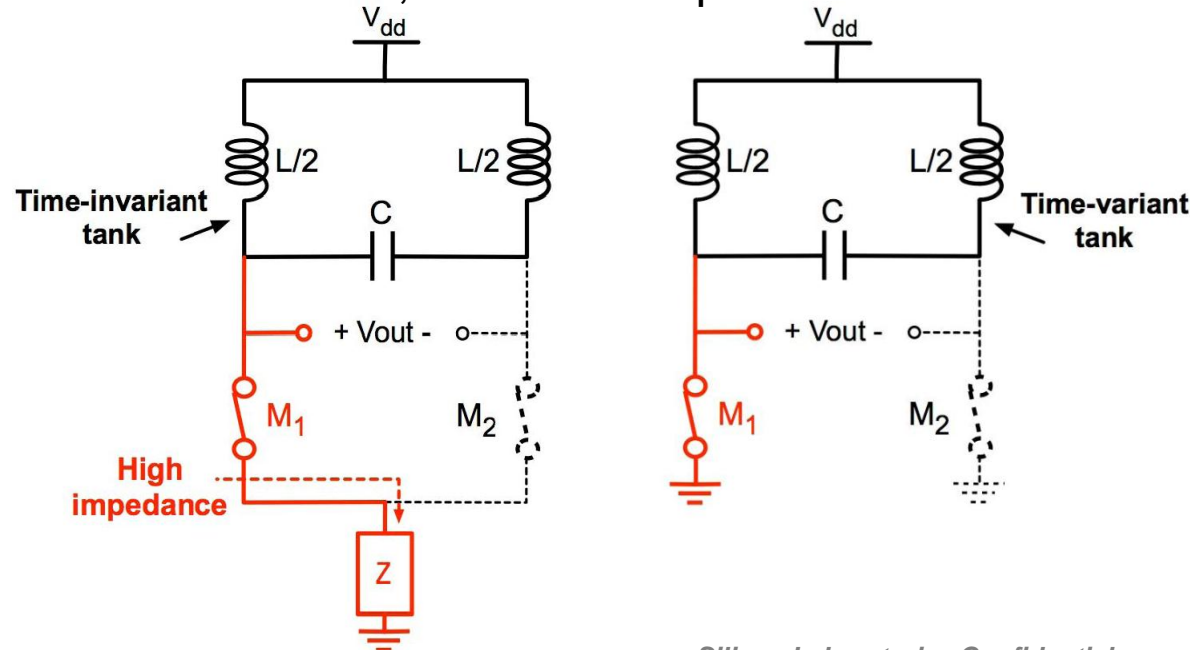
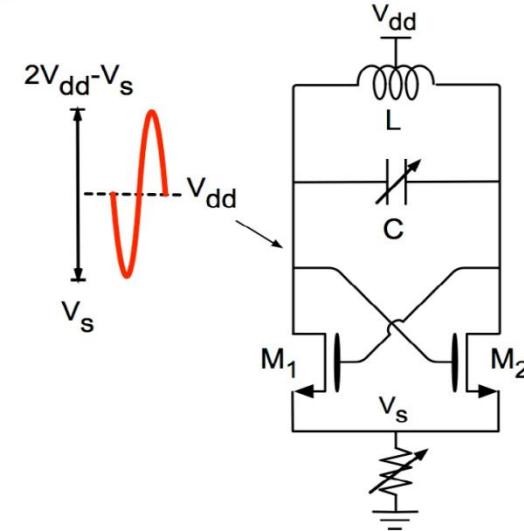
20.1: Class-D VCO

➤ Class-B VCO

- Large swing ($\pm V_{dd}$)
- Need Tail current source (or resistor)
 - Due to R_{on} losses

➤ What if we have very low R_{on} ?

- Go for even higher swings
- Loss in R_{on} is negligible (good switch)
- Lower V_{dd} , hence lower power



20.1: Class-D VCO (cont.)

➤ Operation

- T1: The I_{L_a} charges up
- T2: L_a resonates with C

➤ Circuit equations

- Continuous I_{L_a} and its derivative
- $T1 = T2$ (due to symmetry)

$$V_{peak} = V_{dd} \left(1 + \sqrt{\frac{\pi^2 \alpha^2}{4} + 1} \right) \approx 3.27 V_{dd}$$

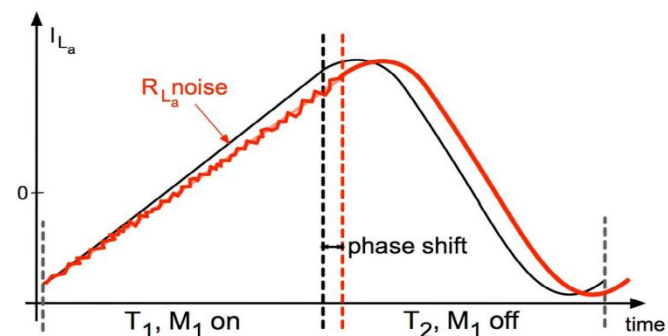
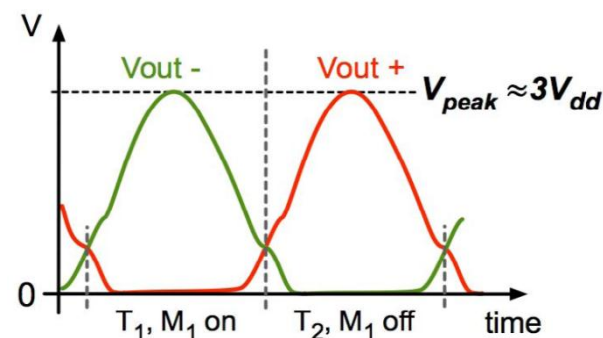
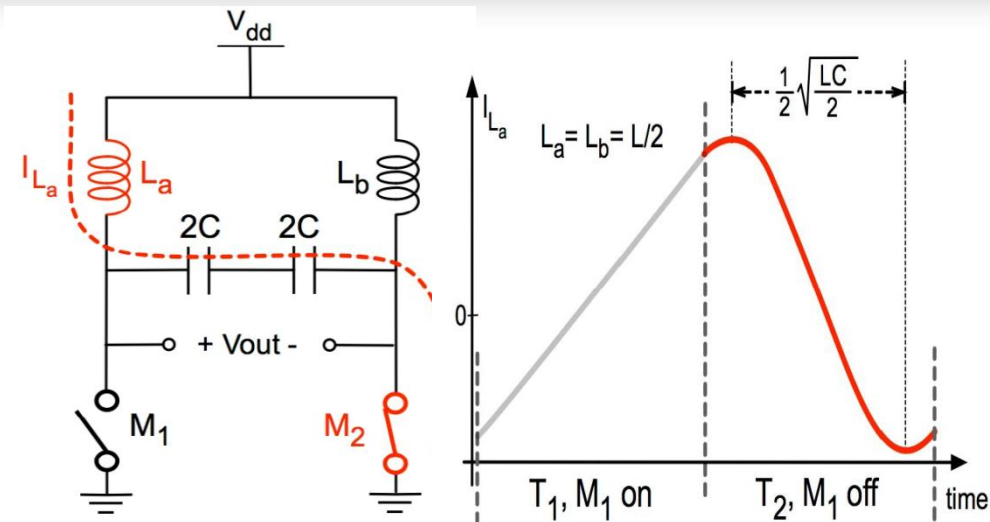
$$\omega_D = \frac{1}{\sqrt{LC}} \frac{\sqrt{2}}{\alpha} \quad \alpha = \frac{1}{2} + \sqrt{\frac{1}{4} + \frac{4}{\pi^2}} \approx 1.3$$

➤ Note that the tank is time variant

- Makes phase noise calculation even more difficult

➤ Very large (1.35mm) switches were used

- Poor $1/f^3$ and supply pushing



20.2: Class F VCO

➤ Motivation: Reduce power

- Larger tail current help PN
- Until the devices go in triode

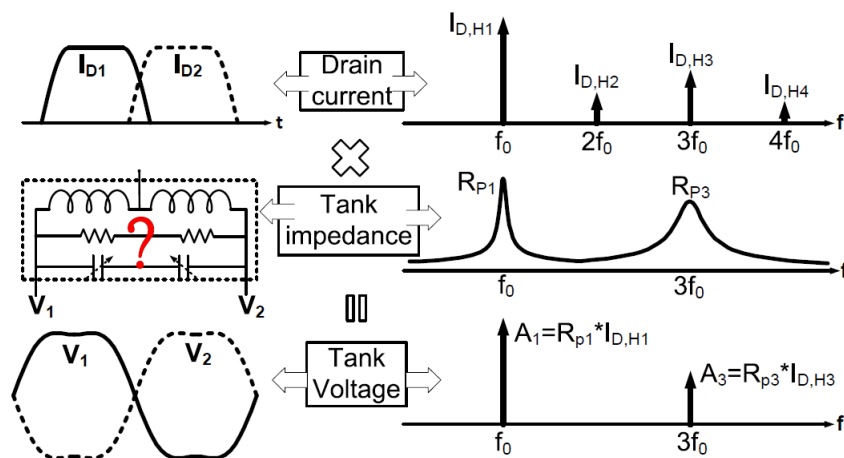
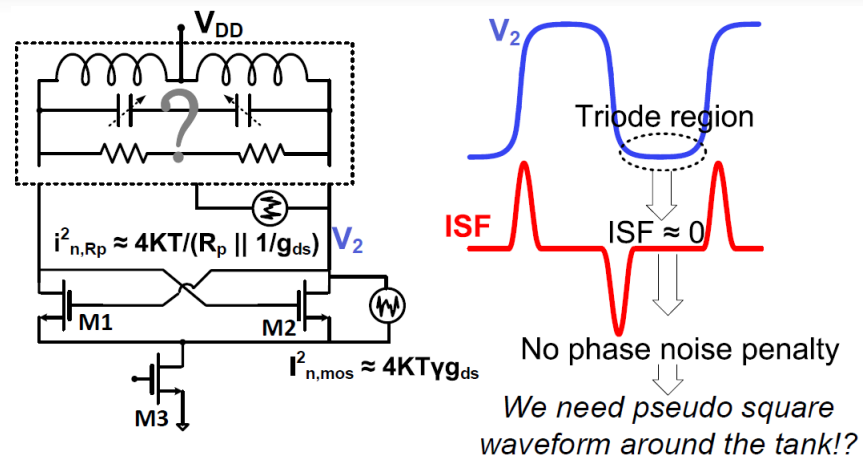
➤ Basic idea: Improve ISF

- Noise injection when V is flat
 - Not during zero crossing
- But how?

➤ Make the tank to have high impedance at f_0 and $3f_0$

➤ Make $Z(3f_0) = \frac{Z(f_0)}{X}$

- A more advanced tank is required



20.2: Class F VCO (cont.)

➤ A transformer-based tank will provide two pair of complex poles

➤ By setting the proper coupling factor, the intended impedance can be achieved

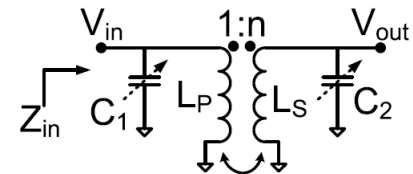
➤ Oscillation at higher frequency

- Lower loop gain
- Injection locking to $3f_1$

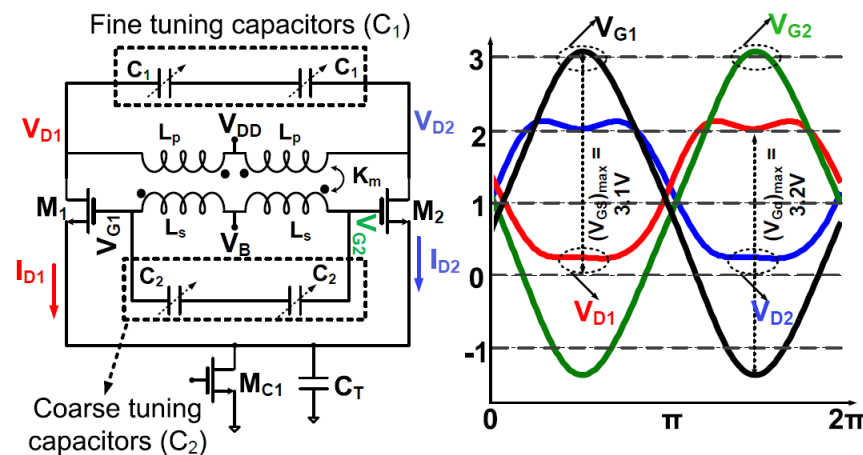
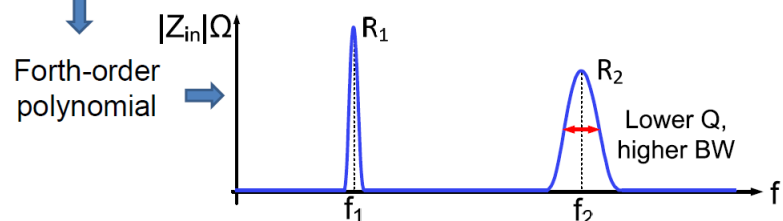
➤ Very large gate voltages

- Use thick-oxide devices

• Transformer based tank has two resonance frequency for imperfect coupling factor.



$$Z_{in} = \frac{s^3(L_p L_s C_2 (1 - K_m^2)) + s(L_p)}{s^4(L_p L_s C_1 C_2 (1 - K_m^2)) + s^2(L_s C_2 + L_p C_1) + 1}$$



• M1 & M2 thick oxide devices → More than 10 years operation



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